

View Online at <https://aerobasegroup.com/nsn/5961-00-394-0297>

Inclosure Material:

Glass all semiconductor device diode

Overall Length:

0.150 inches all semiconductor device diode and 0.170 inches all semiconductor device diode

Terminal Length:

1.000 inches all semiconductor device diode

Overall Diameter:

0.068 inches all semiconductor device diode and 0.076 inches all semiconductor device diode

Internal Configuration:

Junction contact all semiconductor device diode

Internal Junction Configuration:

Pn all semiconductor device diode

Component Function Relationship:

Matched

Component Name And Quantity:

4 semiconductor device diode

Mounting Method:

Terminal all semiconductor device diode

Field Force Effect Type:

Electrostatic charge

Features Provided:

Electrostatic sensitive and hermetically sealed case

Semiconductor Material:

Silicon all semiconductor device diode

Voltage Rating In Volts Per Characteristic:

15.0 breakdown voltage, dc all semiconductor device diode and 41.0 forward voltage, dc all semiconductor device diode

Current Rating Per Characteristic:

100.00 nanoamperes forward current, average peak all semiconductor device diode

Power Rating Per Characteristic:

250.0 milliwatts small-signal input power, common-collector preset all semiconductor device diode

Maximum Operating Temperature Per Measurement Point:

125.0 degrees celsius junction all semiconductor device diode

Terminal Type And Quantity:

2 uninsulated wire lead all semiconductor device diode

Shelf Life:

N/a

Unit Of Measure:

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Demilitarization:

No

Fig:

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